

Title of Change:	Update NVH820S75L4SPC data sheet from rev.6 to rev.7.	
Effective date:	15 Oct 2021	
Contact information:	Contact your local onsemi Sales Office or SayMeng.Lim@onsemi.com	
Type of notification:	This Product Bulletin is for notification purposes only. onsemi will proceed with implementation of this change upon publication of this Product Bulletin.	
Change Category:	Datasheet Change	
Change Sub-Category(s):	Datasheet/Product Doc change	
Sites Affected:		
onsemi Sites	External Foundry/Subcon Sites	
None	None	
Description and Purpose:		
<p>This is an updated Product Bulletin to correct the typo in PB24257Z “Title of Change” and this Product Bulletin is to inform that, onsemi is updating the NVH820S75L4SPC datasheet with the following changes and justifications</p> <ul style="list-style-type: none">1. Change description: Remove the maximum di/dt (IGBT) & maximum dv/dt (IGBT) from the <i>Absolute Maximum Rating</i> Table (Page 3) Purpose: Guidance on maximum di/dt and dv/dt slew rates available in Application Notes upon request.2. Change description: Update Err (Reverser Recovery Energy) test condition from Rg.on=8Ω to Rg.on=4Ω in <i>Characteristics of Inverse Diode</i> Table (Page 5) Purpose: typo correction.3. Change description: Add fluid temperature (Tf) 25°C vs. pressure drop characteristic curve in <i>Figure 20: Pressure Drop in Cooling Circuit</i> (Page 9). Purpose: Additional operating condition to aid customer’s cooling structure design.		
List of Affected Standard Parts:		
Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the <u>PCN Customized Portal</u> .		
NVH820S75L4SPC		